

ABSTRACT

5 An object of the present invention is to provide a  
low-resistance n-type Group III nitride semiconductor  
layered structure having excellent flatness and few pits.

10 The inventive n-type group III nitride semiconductor  
layered structure comprises a substrate and, stacked on  
the substrate, an n-type impurity concentration periodic  
variation layer comprising an n-type impurity atom higher  
concentration layer and an n-type impurity atom lower  
concentration layer, said lower concentration layer being  
stacked on said higher concentration layer.